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Table 1.2: The commonly studied compositions for phase change materials in optical data storage and PCRAM.

Table 4.1: Value of constant B, apparent activation energy for glass transition $E_{gl}$, $n$, $m$, activation energy for crystallization $E_c$(MK), $E_c$(ME) for Sn$_{10}$Sb$_{20}$Se$_{70-x}$Te$_x$ ($0 \leq X \leq 12$) compositions.

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